

N.I.	Champal	4E \/	(D C)	Davis	MACCEET
<b>I7</b> -	Cnannei	40 V	(D-2)	rower	<b>MOSFET</b>

PRODUCT SUMMARY							
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ) (TYP.)	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)				
45	1.1 at V <sub>GS</sub> = 10 V	210	72 nC				

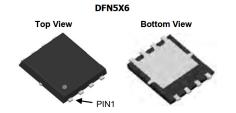
#### **FEATURES**

- DT-SGT Power MOSFET
- 100 %  $R_{\rm g}$  and UIS Tested
- AEC-Q101 Qualified for Automotive Applications



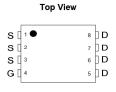
#### **APPLICATIONS**

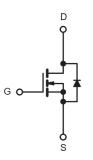
- Networking
- Load Switch



**Din-Tek** 

**SEMICONDUCTOR** 





N-Channel MOSFET

PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	45	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		
Gate-Source Voltage		V <sub>GS</sub>	± 20	- V	
Continuous Proin Current (T = 150 °C)	T <sub>C</sub> = 25 °C		210		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	185	_	
Pulsed Drain Current		I <sub>DM</sub>	800	A	
Avalanche Current		I <sub>AS</sub>	157		
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	739	mJ	
Maximum Power Dissipation 8	T <sub>C</sub> = 25 °C	В	178 <sup>b</sup>	w	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 70 °C	P <sub>D</sub>	113 b	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	20	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.65	C/VV		

#### Notes

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	STMBOL	TEST CONDITIONS	IVIIIV.	III.	WAX.	UNIT
	.,		T			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	45	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	2	-	4	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 45 V, V <sub>GS</sub> = 0 V		-	1	μA
<u> </u>	500	$V_{DS} = 36 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$	-	-	10	μ/.
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS}\!\geq 10~V,~V_{GS}=10~V$	190	-	-	Α
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	1.1	1.25	mΩ
Forward Transconductance a	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	-	85	-	S
Dynamic <sup>b</sup>				•		
Input Capacitance	C <sub>iss</sub>		-	4080	-	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	985	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	17	-	
Total Gate Charge <sup>c</sup>	Qg		-	72		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	49	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	16	-	
Gate Resistance	$R_g$	f = 1 MHz		1.0		Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	13	-	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 20 \text{ V}, R_{I} = 2 \Omega$	-	15	-	
Turn-Off Delay Time c	t <sub>d(off)</sub>	$I_D = 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 3 \Omega$	-	38	-	ns
Fall Time <sup>c</sup>	t <sub>f</sub>		-	26	-	
Drain-Source Body Diode Ratings ar	d Characteri	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)	<b>-</b>			
Continuous Source Current	Is	T <sub>C</sub> = 25 °C	-	-	210	А
Pulsed Source Current	I <sub>SM</sub>		-	-	800	Α
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V	-	-	1.2	V
Reverse Recovery Time	t <sub>rr</sub>		-	60	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/μs	_	136	_	иC

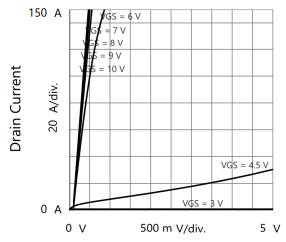
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

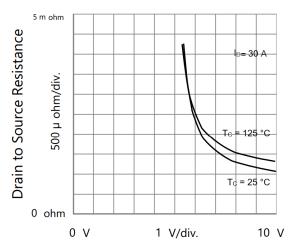
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



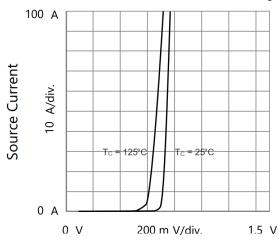
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



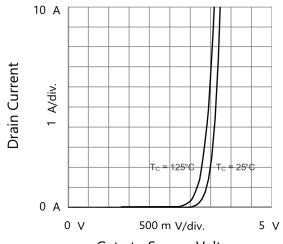
Drain to Source Voltage Output Characteristics



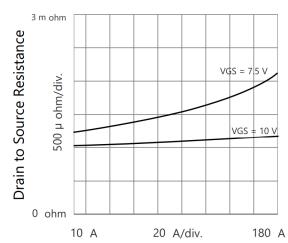
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



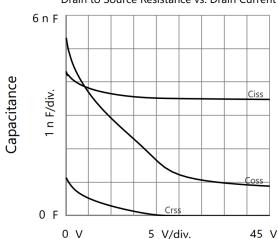
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



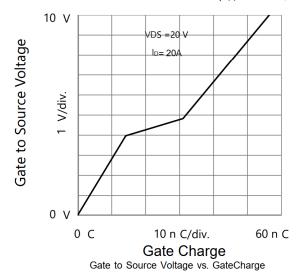
Drain Current
Drain to Source Resistance vs. Drain Current

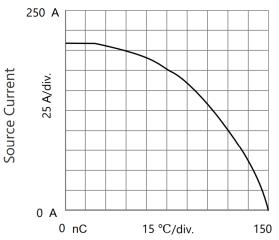


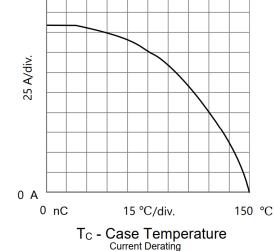
Drain to Source Voltage Capacitances

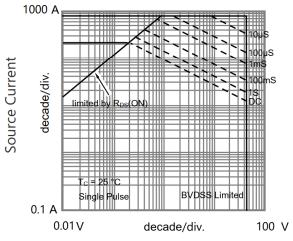


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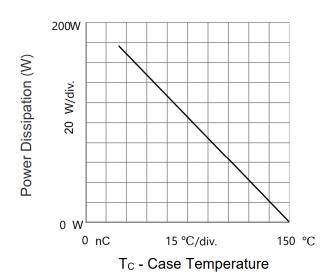


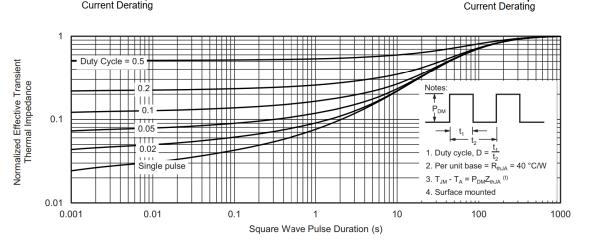








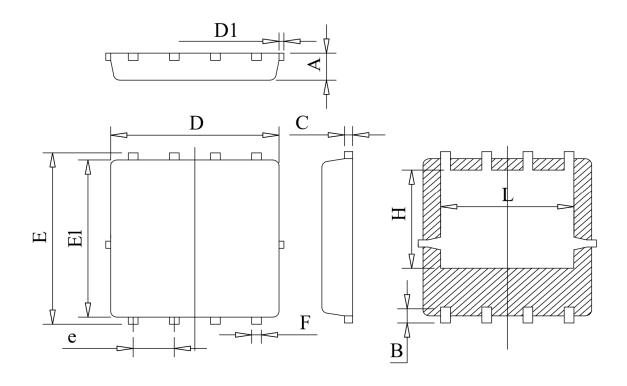




Normalized Thermal Transient Impedance, Junction-to-Ambient



## **DFN5X6-8L PACKAGE OUTLINE**



# **COMMON DIMENSIONS** (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25





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